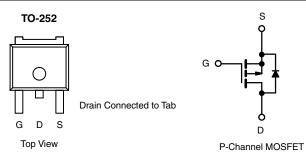


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Vishay Siliconix

# Automotive P-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 80			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.025			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.031			
I <sub>D</sub> (A)	- 50			
Configuration	Single			



#### **FEATURES**

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified<sup>d</sup>
- 100 % R<sub>a</sub> and UIS Tested
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P08-25L-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		$V_{DS}$	- 80	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	L	- 50		
	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	- 28		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 50	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 120		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 45		
Single Pulse Avalanche Energy	L=0.1 IIII	E <sub>AS</sub>	100	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	136	W	
	T <sub>C</sub> = 125 °C		45	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	50	°C/W	
Junction-to-Case (Drain)		$R_{thJC}$	1.1	C/VV	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static		-						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 80	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA		- 2.0	- 2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 80 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 80 V, T <sub>J</sub> = 125 °C	-	-	- 50	μA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 80 V, T <sub>J</sub> = 175 °C	-	-	- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 12.5 A	-	0.020	0.025		
Dunin Course On Otata Basistanas		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 12.5 A, T <sub>J</sub> = 125 °C	-	-	0.044		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 12.5 A, T <sub>J</sub> = 175 °C	-	-	0.055	Ω	
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 10.5 A	-	0.025	0.031		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = -	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 12.5 A		38	=-	S	
Dynamic <sup>b</sup>		<u> </u>					•	
Input Capacitance	C <sub>iss</sub>			-	4279	5350	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 25 V, f = 1 MHz	-	356	445		
Reverse Transfer Capacitance	C <sub>rss</sub>	7		-	239	300		
Total Gate Charge <sup>c</sup>	Qg			-	91	137		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -40 \text{ V}, I_{D} = -12.5 \text{ A}$	-	8.2	=-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	24	=-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.60	3.26	5.00	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	10	15		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 40 V, $R_L$ = 3.2 Ω $I_D$ $\cong$ - 12.5 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 Ω		-	11	17	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	71	107		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	16	24		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>	•						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 120	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = -	10.5 A, V <sub>GS</sub> = 0 V	-	- 0.82	- 1.5	V	

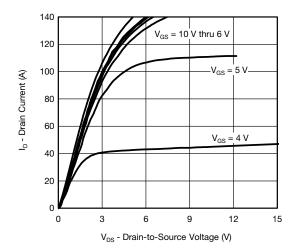
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

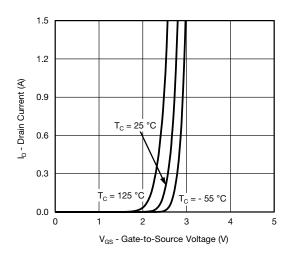
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



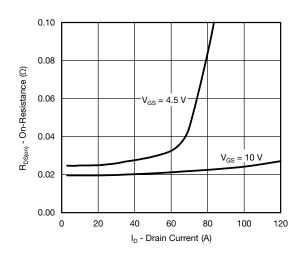
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



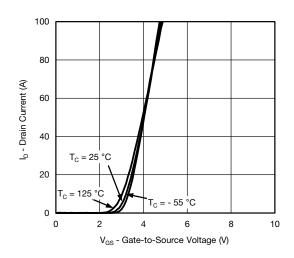
#### **Output Characteristics**



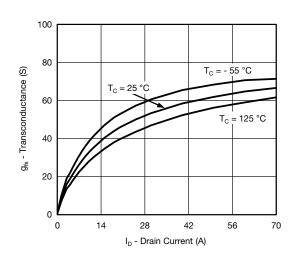
#### **Transfer Characteristics**



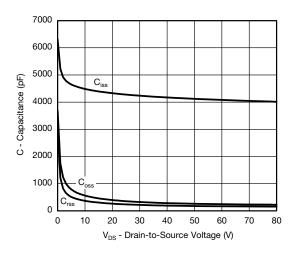
On-Resistance vs. Drain Current



#### **Transfer Characteristics**



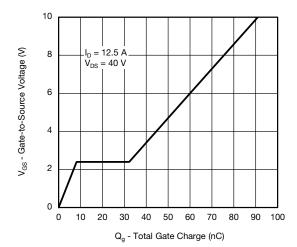
#### Transconductance

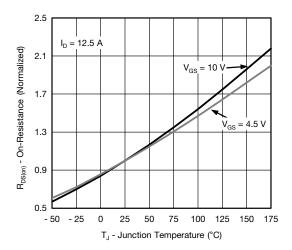


Capacitance

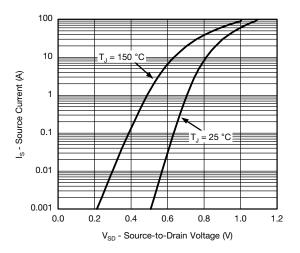


### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

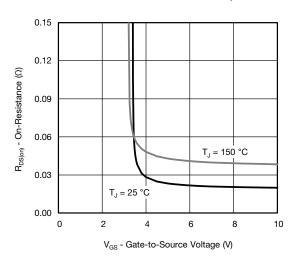




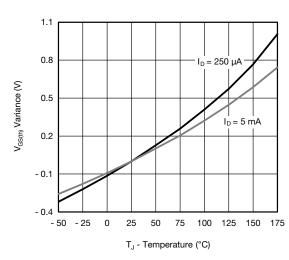
#### **Gate Charge**



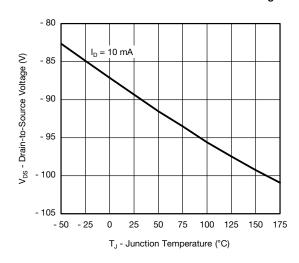
On-Resistance vs. Junction Temperature



#### **Source Drain Diode Forward Voltage**



On-Resistance vs. Gate-to-Source Voltage

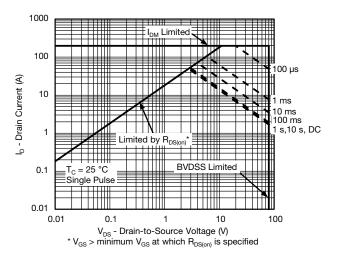


**Threshold Voltage** 

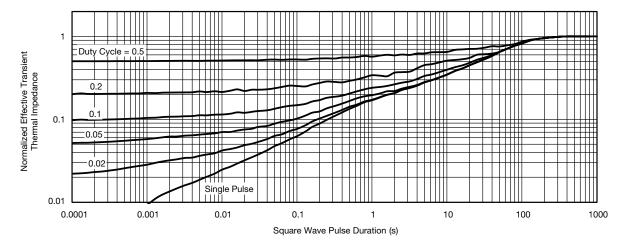
**Drain Source Breakdown vs. Junction Temperature** 

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## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



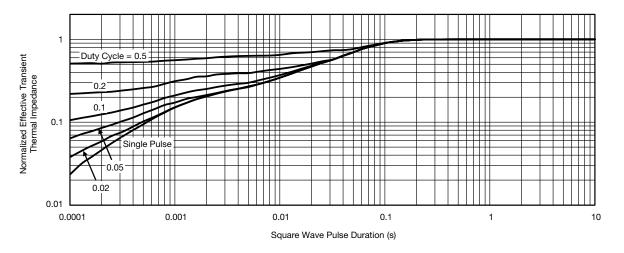
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

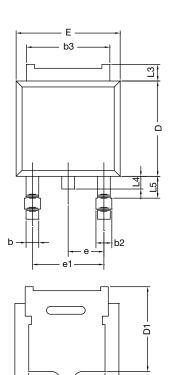
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

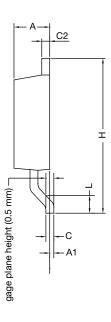
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# **TO-252AA Case Outline**





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

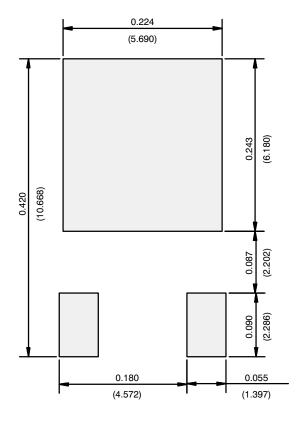
DWG: 6019

#### Note

• Dimension L3 is for reference only.



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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